

TO-251S Plastic-Encapsulate MOSFETS

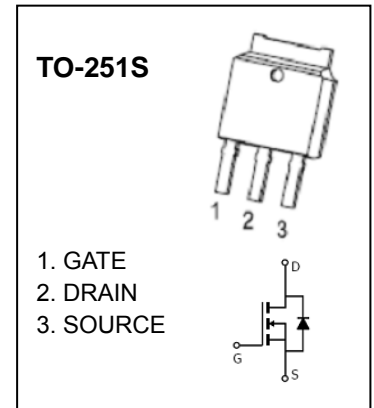
CJD04N60B 600V N-Channel Power MOSFET

General Description

This advanced high voltage MOSFET is designed to withstand high energy in the avalanche mode and switch efficiently. This new high energy device also offers a drain-to-source diode with fast recovery time. Designed for high voltage, high speed switching applications such as power supplies, converters, power motor controls and bridge circuits.

FEATURE

- High Current Rating
- Lower $R_{ds(on)}$
- Lower Capacitance
- Lower Total Gate Charge
- Tighter V_{SD} Specifications
- Avalanche Energy Specified



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	I_D	4.0	A
Pulsed Drain Current	I_{DM}	16	
Single Pulsed Avalanche Energy (note1)	E_{AS}	260	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	
Maximum Lead Temperature for Soldering Purposes , 1/8" from Case for 5 Seconds	T_L	260	

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	600			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			25	μA
		V _{DS} =0.8xRatedV _{(BR)DSS} , V _{GS} =0V, T _J =125°C			100	
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =± 30V			± 100	nA
On characteristics (note2)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.0A		2.3	3.0	Ω
Forward transconductance	g _{fs}	V _{DS} =50V, I _D =2.0A	2.5			S
Dynamic characteristics (note 3)						
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz			760	pF
Output capacitance	C _{oss}				180	
Reverse transfer capacitance	C _{rss}				20	
Switching characteristics (note 2,3)						
Turn-on delay time	t _{d(on)}	V _{DD} =300V, V _{GS} =10V, R _G =9.1Ω, I _D =4.0A			20	ns
Turn-on rise time	t _r				10	
Turn-off delay time	t _{d(off)}				40	
Turn-off fall time	t _f				20	
Total gate charge	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =4.0A,		5.0	10	nC
Gate to source charge	Q _{GS}			2.7		
Gate to drain "miller" charge	Q _{GD}			2.0		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note2)	V _{SD}	V _{GS} = 0V, I _S =4.0A			1.5	V
Continuous drain-source diode forward current(note4)	I _S				10	A
Pulsed drain-source diode forward current	I _{SM}				40	A

Notes :

1. L=30mH, I_L=4A, V_{DD}=100V, V_{GS}=10V, R_G=25Ω, Starting T_J=25°C.
2. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.
3. Guaranteed by design, not subject to production
4. Surface mounted on FR4 board, t≤10s

